



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-252 Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

FEATURES

- Low speed switching

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	100	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

TO-252



1. BASE
2. COLLECTOR
3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}$, $I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}$, $I_E=0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30\text{V}$, $I_B=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}$, $I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}$, $I_B=-0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}$, $I_B=-0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-0.1\text{A}$ $f=10\text{MHz}$	50	80		MHz

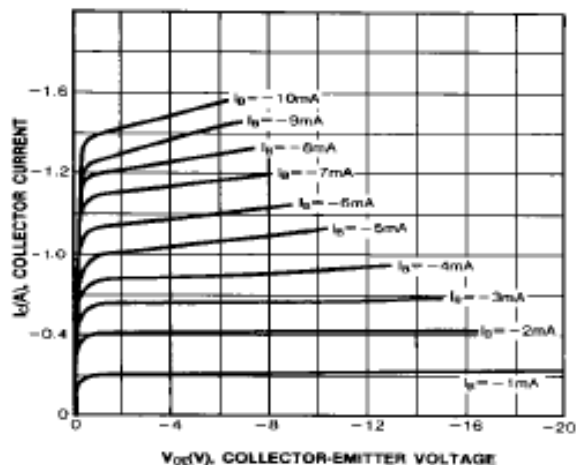
CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

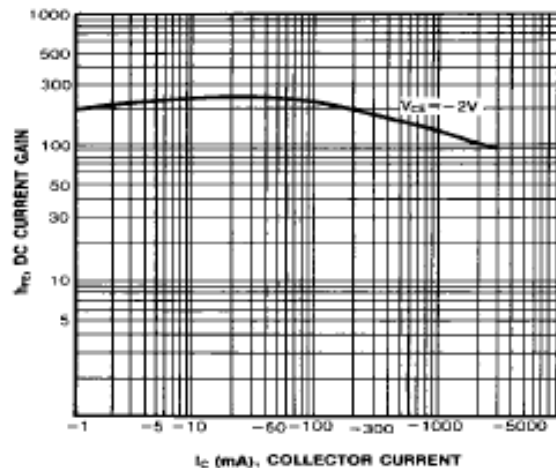
Typical characteristics

B772

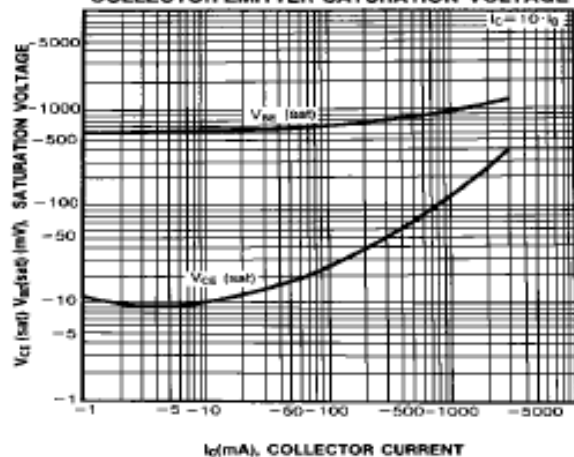
STATIC CHARACTERISTIC



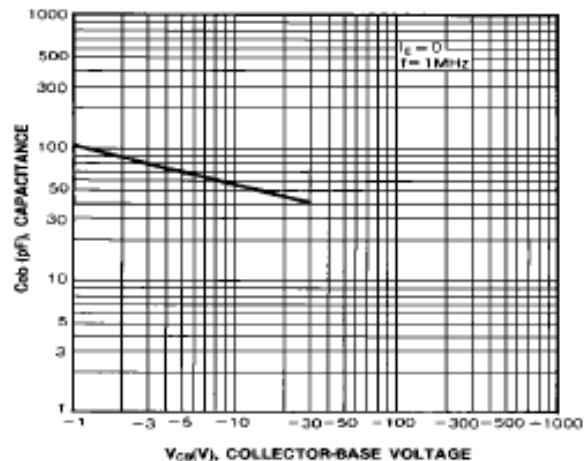
DC CURRENT GAIN



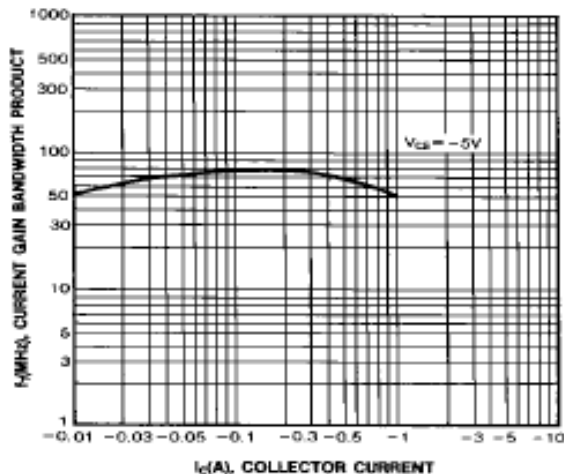
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



CURRENT GAIN-BANDWIDTH PRODUCT



SAFE OPERATING AREA

